

Dual N-channel TrenchMOS standard level FET 23 April 2013 Pi

Product data sheet

1. General description

Dual standard level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} > 1 V @ 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>		-	-	27	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	32	W
Static characte	eristics FET1 and FET2						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>		-	21.25	25	mΩ
Dynamic characteristics FET1 and FET2							
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \text{Fig. 14}; \text{Fig. 15}$		-	2.6	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

6. Ordering information

Table 3. Ordering in	formation						
Type number	Package						
	Name	Description	Version				
BUK7K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K25-40E	72540E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V _{DGR}	drain-gate voltage	R_{GS} = 20 k Ω ; $T_j \ge 25 \text{ °C}$; $T_j \le 175 \text{ °C}$	-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	-	27	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	19	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	107	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	32	W
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode FET1 and FET2		-	1	1	
l _S	source current	T _{mb} = 25 °C		-	27	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	107	А
Avalanche Ruggedness FET1 and FET2						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_{D} = 28 \text{ A}; V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; \underline{Fig. 3}$	[1][2]	-	10	mJ

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

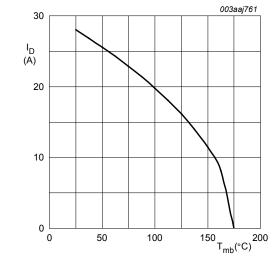
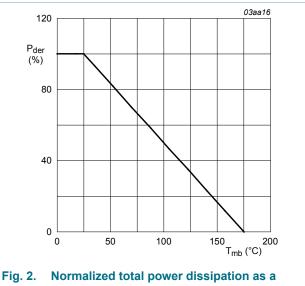


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

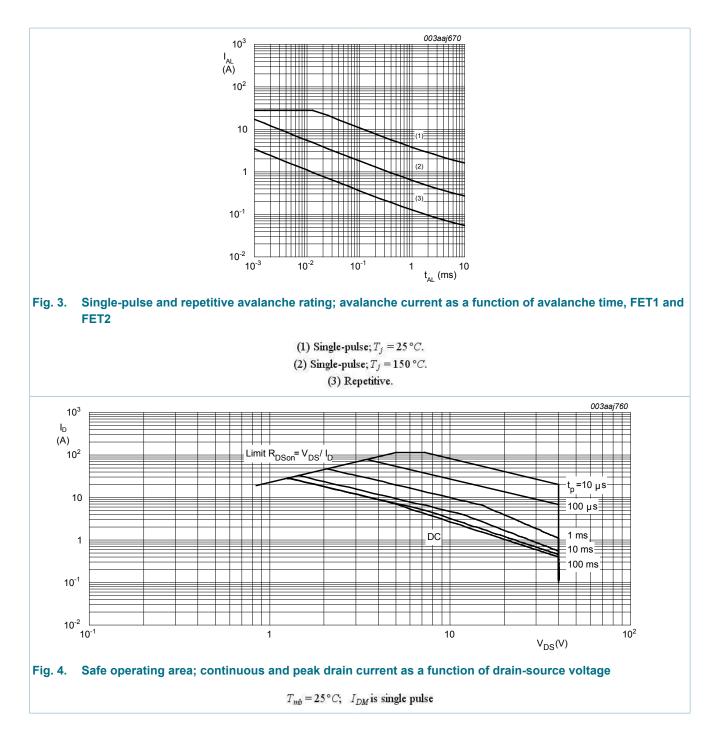


function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	4.68	K/W

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ymbol	Parameter	Condition	S		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			Minimum footprint; mounted on a printed circuit board		-	95	-	K/W
(K/W) 1							003aaj557	
10-1					P		$\delta = \frac{t_p}{T}$	
10 ⁻²	ngle shot	10 ⁻⁴	10 ⁻³	10 ⁻²	10 ⁻¹	$t_p \leftarrow T \rightarrow T$		

10. Characteristics

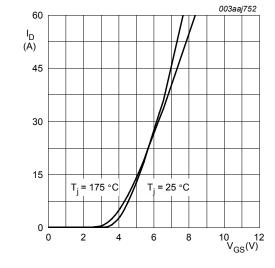
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics FET1 and FET2	· · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	4.5	V
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	21.25	25	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 13	-	40.1	49.3	mΩ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	T2					
Q _{G(tot)}	total gate charge	I_D = 5 A; V_{DS} = 32 V; V_{GS} = 10 V;		-	7.9	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14;</u> <u>Fig. 15</u>		-	1.5	-	nC
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 14}; \text{ Fig. 15}$		-	2.6	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C		-	394	525	pF
C _{oss}	output capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>		-	107	128	pF
C _{rss}	reverse transfer capacitance			-	76	104	pF
t _{d(on)}	turn-on delay time	V_{DS} = 32 V; R _L = 6.5 Ω; V _{GS} = 10 V;		-	4.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$		-	4.5	-	ns
t _{d(off)}	turn-off delay time			-	8.3	-	ns
t _f	fall time	-		-	5.2	-	ns
Source-dra	in diode FET1 and FET2	1	11				
V _{SD}	source-drain voltage	I_{S} = 5 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>		-	0.78	1.2	V
t _{rr}	reverse recovery time	I_{S} = 5 A; d I_{S} /dt = -100 A/µs; V _{GS} = 0 V;		-	12.4	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C		-	6.7	-	nC





 $V_{DS} = 10V$

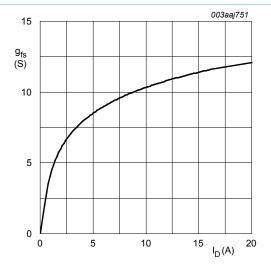
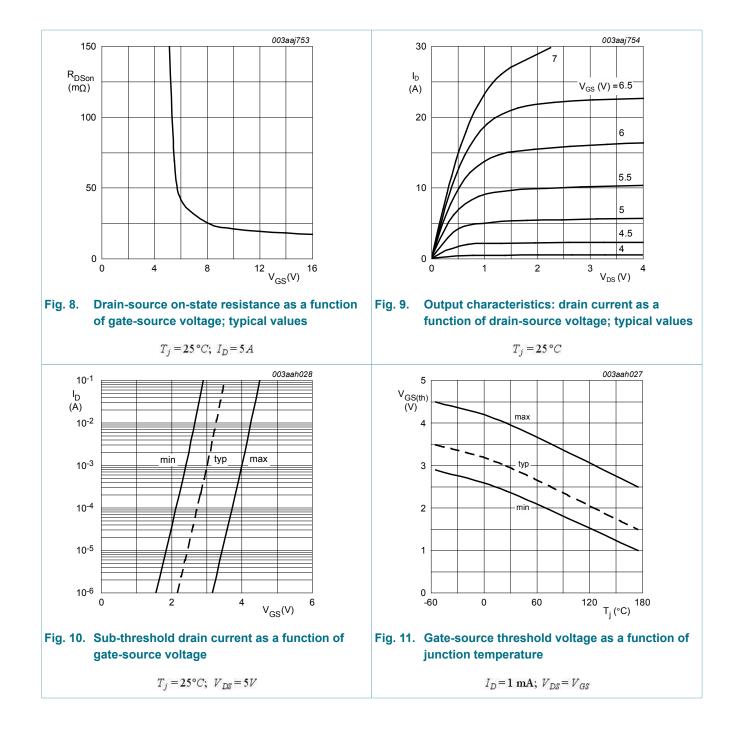


Fig. 7. Forward transconductance as a function of drain current; typical values

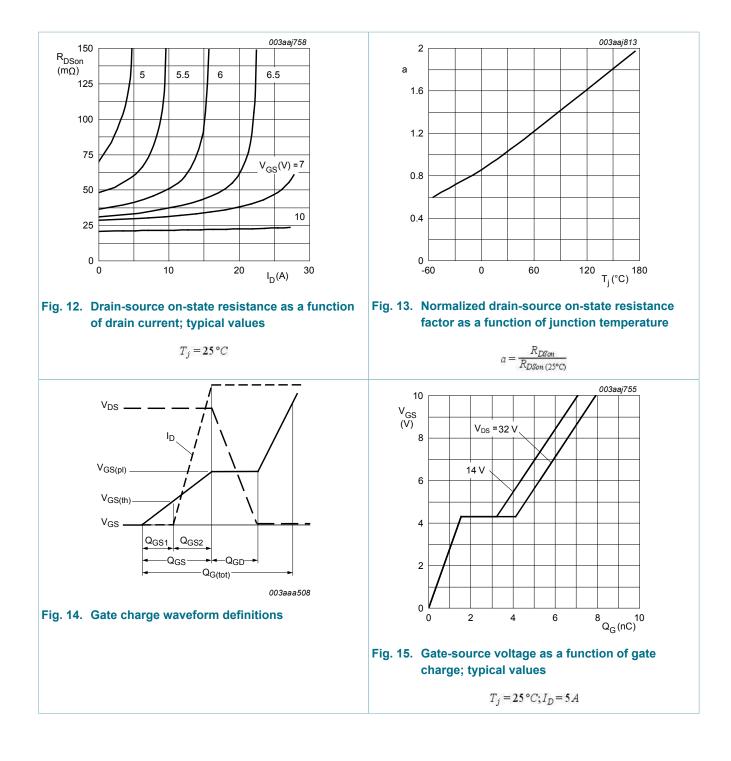
 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$

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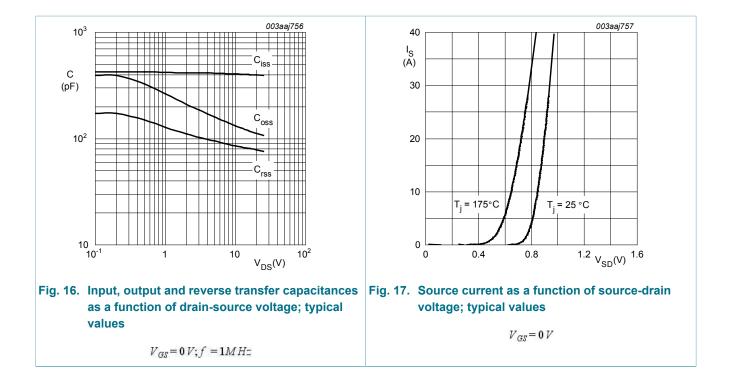
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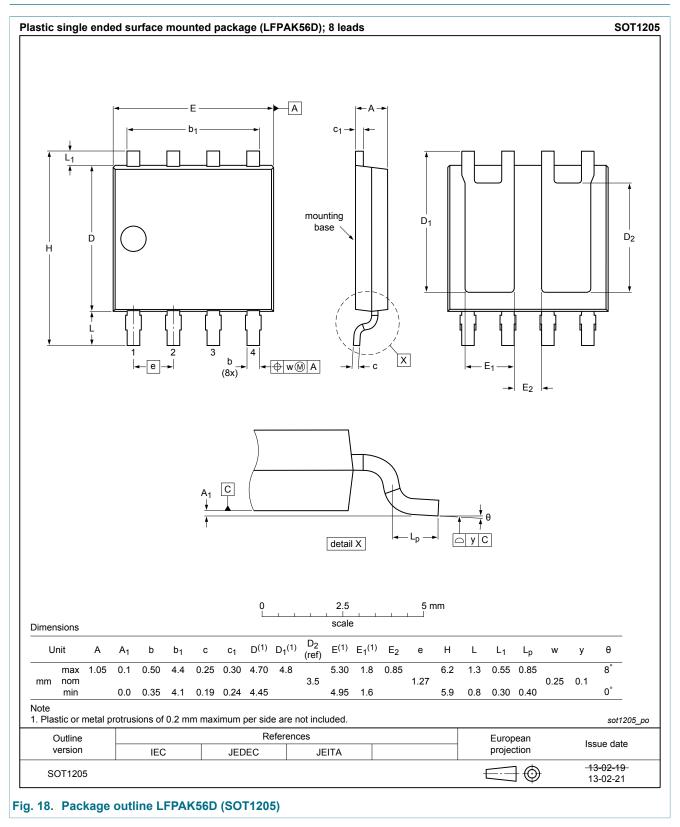
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11. Package outline



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12. Legal information

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